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Honda et al.

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(54) **EPOXY RESIN COMPOSITION, LAMINATE FILM USING THE SAME, AND SEMICONDUCTOR DEVICE**

FOREIGN PATENT DOCUMENTS

JP 10335389 12/1998

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OTHER PUBLICATIONS

Nitto Technical Report vol. 36, No. 1 pp24-29 (1989).

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* cited by examiner

(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

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(21) Appl. No.: **09/548,614**

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(57) **ABSTRACT**

(30) **Foreign Application Priority Data**

Apr. 14, 1999 (JP) 11-106571

An epoxy resin composition comprising an epoxy resin containing 0–10% by weight of a 2-nucleus compound and 50–100% by weight of 3 to 5-nucleus compounds combined and having a dispersity (Mw/Mn) of up to 1.7, an inorganic filler, a curing catalyst, a thermoplastic resin, and an optional phenolic resin and having a Tg of lower than 15° C. in an uncured state is effective in forming a flexible film which is easy to work at room temperature. Owing to the thermoplastic resin added, the composition avoids the problem that when a semiconductor chip is sealed with an uncured film of the composition, the film will lose its original shape or entrapped voids will be formed near the chip.

(51) **Int. Cl.**⁷ **H01L 29/12**

(52) **U.S. Cl.** **428/620; 428/414; 523/466; 525/100; 525/107; 525/165; 525/178; 525/476; 525/529**

(58) **Field of Search** 523/466; 428/416, 428/620; 525/100, 107, 165, 178, 476, 529; 528/31, 32, 38, 42

(56) **References Cited**

U.S. PATENT DOCUMENTS

6,210,811 B1 * 4/2001 Honda et al. 428/620

9 Claims, 1 Drawing Sheet

FIG.1

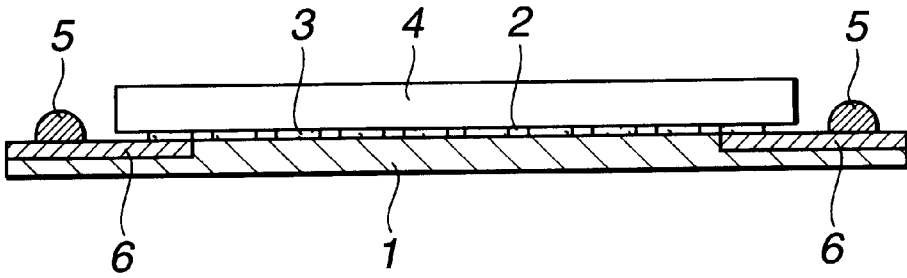


FIG.2

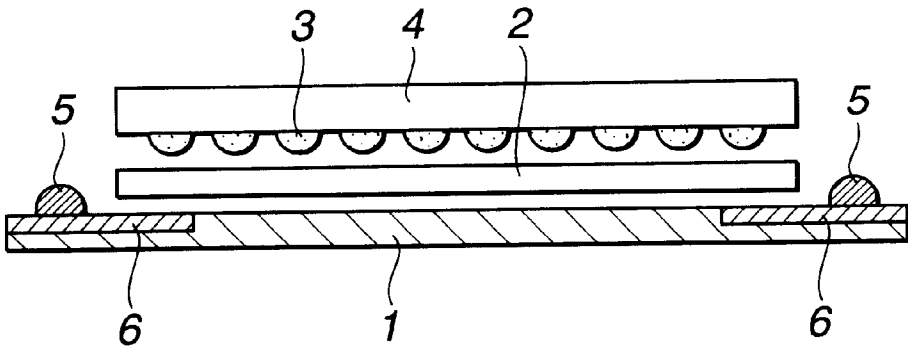
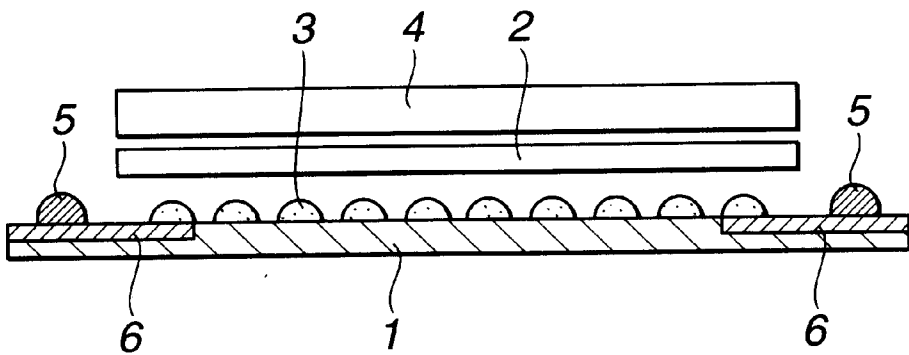


FIG.3



EPOXY RESIN COMPOSITION, LAMINATE FILM USING THE SAME, AND SEMICONDUCTOR DEVICE

This invention relates to an epoxy resin composition of self-polymerization or phenolic curing type, a laminate film using the same and suited for semiconductor packaging, and a semiconductor device sealed with the laminate film.

BACKGROUND OF THE INVENTION

The recent trend of electronic equipment is characterized by high speeds of size and weight reduction. Under the circumstances, it is desired to reduce the size and weight of semiconductor devices serving as the brain of electronic equipment. The ultimate target is to reduce the packaging area to the chip size, realizing a chip size package (CSP).

Epoxy resins are widely used in constructing semiconductor packages because of their good adhesion, heat resistance and moisture resistance. As the package system is diversified as mentioned above, epoxy resins are now used not only as the encapsulants well known in the art, but also as coating, die bonding and underfill materials. Most such materials are diluted with solvents or in paste form.

Of these, the solvent-diluted materials require an attention to carefully remove the solvent that volatilizes off on use, from the standpoints of the health maintenance and safety of workers, undesirably adding to the cost.

Coating materials are used in several ways. One proposed method is to cover the surface of a semiconductor chip solely with a thin film of an epoxy resin composition to effect sealing. It is also proposed to screen print an epoxy resin composition in paste form. These materials include paste-like epoxy resin compositions such as those of the acid anhydride curing type and the amine curing type which are well known in the art. Alternatively, these paste-like epoxy resin compositions may take the form of a film which has been converted to B-stage.

Most of the prior art die bonding and underfill materials were paste-like epoxy resin compositions. Recently, films formed from paste-like die bonding materials are widely utilized. On use, a film is pressed against a lead frame or substrate, and a semiconductor chip is joined onto the film whereupon the film is cured. Most of these die bonding materials are epoxy resin compositions of the acid anhydride curing type and the amine curing type which are well known in the art.

These B-staged films are easier to handle than paste-like materials and provide a very promising system that contributes to the simplification of a semiconductor device fabricating process. However, the epoxy resin compositions of the acid anhydride curing type and the amine curing type are insufficient in the storage of uncured compositions and the moisture resistance and high-temperature performance of cured compositions. They are unsatisfactory in directly covering the semiconductor chip surface with a thin film.

As compared with the epoxy resin compositions of the acid anhydride curing type and the amine curing type, epoxy resin compositions of the self-polymerization type, especially those using imidazoles as the curing catalyst, and epoxy resin compositions of the phenolic curing type are satisfactory in the storage of uncured compositions and the moisture resistance and high-temperature performance of cured compositions, but are difficult to control the progress of reaction and hence, to form B-staged films. To obtain flexible, easy-to-work films, the softening point of an epoxy resin base and a phenolic resin curing agent must be low-

ered. Undesirably, this is done at the expense of the heat resistance of cured compositions.

To solve the above problem, we proposed in U.S. Ser. No. 09/404,301 U.S. Pat. No. 6,210,811 an epoxy resin composition comprising (A) an epoxy resin containing up to 10% by weight of a 2-nucleus compound and at least 50% by weight of 3 to 5-nucleus compounds combined and having a dispersity of up to 1.7, (B) an inorganic filler, and (C) a curing catalyst, the epoxy resin composition in an uncured state having a glass transition temperature of lower than 15° C.

Even an epoxy resin composition of self-polymerization or phenolic curing type can find a good compromise between the flexibility of uncured composition and the heat resistance of cured composition as long as the dispersity or molecular weight distribution of the epoxy resin is properly controlled.

Regrettably, a film material in the form of an epoxy resin composition of self-polymerization or phenolic curing type becomes extremely low in melt viscosity upon heating because both the epoxy resin and phenolic resin used as constituent components are of low molecular weight. Then, when the film is moderately attached to a substrate or board under pressure or when the film is then cured, there will occur, depending on the shape of a device or package and the moderate pressing and curing conditions of the film, a problem that the film loses its original shape or entrapped voids are formed near irregularities on the device.

An object of the invention is to provide an epoxy resin composition of the self-polymerization type or the phenolic curing type which, owing to the addition of a thermoplastic resin of linear molecular structure having a specific molecular weight, avoids the problem that when the gap between a semiconductor chip and a substrate or the surface of a semiconductor chip is sealed with an uncured film of the composition, the film will lose its original shape or entrapped voids are formed near the chip, and which has a low glass transition temperature in an uncured state while maintaining the heat resistance, moisture resistance and low stress of a cured composition.

Another object of the invention is to provide a laminate film comprising a flexible, easy-to-work thin layer of the epoxy resin composition.

A further object of the invention is to provide a semiconductor device in which the gap between a semiconductor chip and a substrate or the surface of a semiconductor chip is sealed with the laminate film.

SUMMARY OF THE INVENTION

The invention is directed at an epoxy resin composition comprising an epoxy resin containing up to 10% by weight of a 2-nucleus compound and at least 50% by weight of 3 to 5-nucleus compounds combined and having a weight average molecular weight (Mw)/number average molecular weight (Mn) ratio (referred to as a dispersity or Mw/Mn, hereinafter) of up to 1.7, an inorganic filler, a curing catalyst, and optionally a phenolic resin, and having a glass transition temperature (often abbreviated as Tg) of lower than 15° C. in an uncured state. When the composition is of the self-polymerization type, an imidazole is preferably used as the curing catalyst. When the composition is of the phenolic curing type, a phenolic resin having a Tg of lower than 15° C. and free of a monomer is preferably used as the curing catalyst. Further preferably, a copolymer obtained by reacting an aromatic polymer with an organopolysiloxane is blended in the composition. Still further preferably, the

composition has a volatile content of up to 0.1% by weight. We have found that by compounding a thermoplastic resin, especially a thermoplastic resin of linear molecular structure having a number average molecular weight of 5,000 to 200,000 in any of the foregoing compositions, the resulting composition is effective in forming a film which is very easy to work at room temperature by virtue of its good elasticity and flexibility. By enclosing a semiconductor chip with the film, there is obtained a semiconductor device having improved heat resistance, improved moisture resistance, low stress property, and a minimized void content. The compounding of the thermoplastic resin can avoid the resin flow and short molding problems. The invention is predicated on these findings.

In a first aspect, the invention provides an epoxy resin composition comprising (A) an epoxy resin containing up to 10% by weight of a 2-nucleus compound and at least 50% by weight of 3 to 5-nucleus compounds combined and having a dispersity of up to 1.7, (B) an inorganic filler, (C) a curing catalyst, (D) a thermoplastic resin, preferably a thermoplastic resin of linear molecular structure having a number average molecular weight of 5,000 to 200,000, and optionally, (E) a phenolic resin. The epoxy resin composition in an uncured state has a glass transition temperature T_g of lower than 15° C.

When the phenolic resin (E) is omitted, the epoxy resin composition is of the self-polymerization type wherein the curing catalyst (C) is preferably an imidazole. When the phenolic resin (E) is included, the epoxy resin composition is of the phenolic curing type. The phenolic resin preferably has a glass transition temperature of lower than 15° C. and is free of a monomer. The epoxy resin composition may further contain (F) a copolymer obtained by reacting an aromatic polymer with an organopolysiloxane of the following compositional formula (1):



wherein R represents hydrogen, an amino, epoxy, hydroxyl or carboxyl group-bearing monovalent hydrocarbon group, or an alkoxy group, R' represents a substituted or unsubstituted monovalent hydrocarbon group, "a" is a positive number of 0.001 to 1, "b" is a positive number of 1 to 2, and the sum of "a" and "b" is from 1 to 3, the number of silicon atoms in one molecule is 2 to 1,000, and the number of functional groups R directly attached to silicon atoms in one molecule is at least 1. Further preferably, the epoxy resin composition in an uncured state has a volatile content of up to 0.1% by weight.

In a second aspect, the invention provides a laminate film comprising at least two layers, at least one layer being formed of the epoxy resin composition to a thickness of 20 to 150 μm .

In a third aspect, the invention provides a semiconductor device comprising a semiconductor chip having a surface sealed with the laminate film in a cured state.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 illustrates in cross section a semiconductor package used in Examples and Comparative Examples.

FIG. 2 illustrates one exemplary process of fabricating the semiconductor package.

FIG. 3 illustrates another exemplary process of fabricating the semiconductor package.

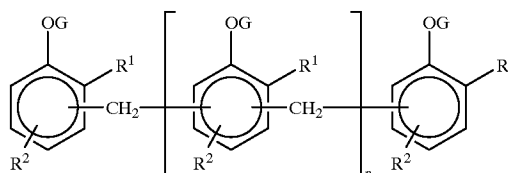
DESCRIPTION OF THE PREFERRED EMBODIMENTS

Epoxy Resin

The epoxy resin used herein is any one of epoxy resins containing up to 10% by weight (i.e., 0 to 10% by weight) of a 2-nucleus or binuclear compound and at least 50% by weight (i.e., 50 to 100% by weight) of 3 to 5-nucleus compounds combined and having a dispersity of up to 1.7 (i.e., 1.0 to 1.7). The dispersity is defined as a weight average molecular weight divided by a number average molecular weight and thus represents a molecular weight distribution. Since the epoxy resin used herein has one epoxy group in each nucleus, an n-nucleus compound has n epoxy groups in one molecule.

Appropriate epoxy resins include novolac type epoxy resins represented by the following formula (2), such as phenol novolac type epoxy resins, cresol novolac type epoxy resins, and phenol and cresol co-condensed novolac type epoxy resins, and trishydroxyphenylalkane type epoxy resins represented by the following formula (3), such as trishydroxyphenylmethane type epoxy resins and trishydroxyphenylpropane type epoxy resins.

(2)

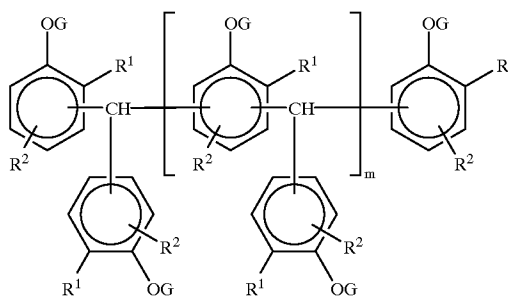


Herein, R¹ is hydrogen or methyl, R² is hydrogen or bromine, G is glycidyl:



and n is 0 or a natural number, preferably an integer of 0 to 5, more preferably 1, 2 or 3.

(3)



Herein, R¹ is hydrogen or methyl, R² is hydrogen or bromine, G is as defined above, and m is 0 or a natural number, preferably an integer of 0 to 5, more preferably 0 or 1.

Most preferred among these are those epoxy resins, in which the content of 3 to 5-nucleus compounds combined is at least 60% by weight (i.e., 60 to 100% by weight), the proportion of the 3-nucleus compound in the total amount of 3 to 5-nucleus compounds is at least 60% by weight (i.e., 60 to 100% by weight), the dispersity is up to 1.5 (i.e., 1.0 to 1.5), and the softening temperature is lower than 10° C., especially cresol novolac type epoxy resins. If the content of the 2-nucleus compound relative to the entire epoxy resin is

too high, the cured composition has a lower Tg and poor heat resistance. Even within an appropriate content of the 2-nucleus compound, if the total amount of 3 to 5-nucleus compounds is too small, indicating a greater proportion of 6 or poly-nucleus compounds, the uncured composition has a higher Tg which deprives the film of its flexibility at room temperature, with a possibility of failure of the film.

In combination with the above-described epoxy resins, any conventional well-known epoxy resin may be used. Such conventional epoxy resins include bisphenol type epoxy resins such as bisphenol A type epoxy resins and bisphenol F type epoxy resins, biphenyl type epoxy resins, naphthalene type epoxy resins, cyclopentadiene type epoxy resins, phenol aralkyl type epoxy resins, and biphenyl aralkyl type epoxy resins. The conventional epoxy resin is blended with the above-described epoxy resin in such amounts that the resulting epoxy resin composition may have a Tg of lower than 15° C.

These epoxy resins should preferably have a total chlorine content of up to 1,500 ppm, more preferably up to 1,000 ppm. When chlorine extraction with water is effected at 120° C. and an epoxy resin concentration of 50% for 20 hours, the epoxy resins should preferably have an extracted chlorine content of up to 5 ppm. If the total chlorine content and the water extracted chlorine content are above the respective limits, the packaged semiconductor would have less reliable moisture resistance.

Filler

The inorganic filler used herein may be selected from various types of fillers depending on a particular application. Exemplary fillers include natural silicas such as crystalline silica and amorphous silica, synthetic high-purity silica, fused silica, synthetic spherical silica, talc, mica, silicon nitride, boron nitride, alumina, and conductive particles such as silver powder, alone or in admixture of two or more. The shape of the inorganic filler is not critical, and spherical, ground and irregular shapes may be used, with the spherical one being preferred. An appropriate amount of the inorganic filler blended is about 50 to 1,000 parts, more preferably about 100 to 400 parts by weight per 100 parts by weight of the entire resin content (that is, the epoxy resin content plus the content of a phenolic resin and/or an aromatic polymer-organopolysiloxane copolymer to be described later, if blended).

The particle size of the inorganic filler is limited by the thickness of a laminate film. Desirably, the maximum particle size of the inorganic filler is less than the laminate film thickness, and the mean particle size is less than 1/2 of the laminate film thickness. Usually, the inorganic filler having a maximum particle size of less than 150 μm, preferably less than 75 μm, and a mean particle size of about 0.1 to 70 μm, more preferably about 1 to 30 μm is used. It is noted that the mean particle diameter can be determined as the weight average value (or median diameter) based on the laser light diffraction technique, for example.

Curing Catalyst

The epoxy resin composition may be formulated to either the self-polymerization where no curing agent is blended or the phenolic curing type where a phenolic resin is blended as the curing agent. In either case, the curing catalyst is blended as an essential component.

For the epoxy resin compositions of the self-polymerization type, any curing catalyst that allows the epoxy resin to polymerize by itself may be used without a need to limit its type. For example, imidazoles and tertiary amines may be used alone or in admixture of two or more. Of these, imidazoles are desirable when the shelf stability of

uncured compositions is taken into account. Exemplary imidazoles include 2-methylimidazole, 2-ethylimidazole, 2-ethyl-4-methylimidazole, 2-phenylimidazole, 2-phenyl-4-methylimidazole, 2-phenyl-4-hydroxymethylimidazole, and 2-phenyl-4,5-di(hydroxymethyl)-imidazole. Exemplary tertiary amines include triethylamine, benzyltrimethylamine, α-methylbenzyltrimethylamine, as well as cycloamidines such as 1,8-diazabicyclo(5.4.0)undecene-7.

For the epoxy resin compositions of the phenolic curing type, organic phosphorus compounds may be used as the curing catalyst as well as the above-described imidazoles and tertiary amines. Exemplary organic phosphorus compounds include organic phosphine compounds and salts thereof such as triphenylphosphine, tributylphosphine, tri(p-tolyl)phosphine, tri(p-methoxyphenyl)phosphine, tri(p-ethoxyphenyl)phosphine, and triphenylphosphine-triphenyl borane, and quaternary phosphonium compounds and salts thereof such as tetraphenylphosphonium-tetraphenyl borate.

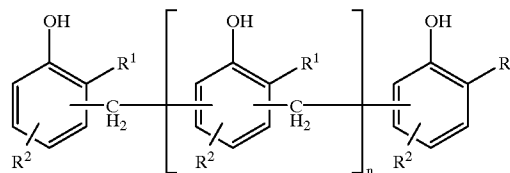
An appropriate amount of the curing catalyst blended is about 0.01 to 10 parts, more preferably about 0.1 to 5 parts by weight per 100 parts by weight of the epoxy resin (or the epoxy resin plus the phenolic resin, if the phenolic resin is blended). If the amount of the curing catalyst is too small, heat molding would result in undesirable undercure. Too large amounts of the curing catalyst can detract from the shelf stability.

Phenolic Resin

For the phenolic curing type epoxy resin composition, phenolic resins are blended as the curing agent.

Any phenolic resin having at least one phenolic hydroxyl group, preferably at least two phenolic hydroxyl groups in a molecule may be used herein. As opposed to the epoxy resin, the molecular weight distribution of the phenolic resin is not critical. In order that the (uncured) epoxy resin composition have a Tg of lower than 15° C., the phenolic resin should desirably have a Tg of lower than 15° C., especially lower than 10° C. Also, in order to avoid the cured composition from losing heat resistance, the phenolic resin should desirably be free of monomers. With these requirements taken into account, the preferred phenolic resins are those phenolic resins in which no monomers are present, the total content of 2- to 4-nucleus compounds is at least 80% by weight (i.e., 80 to 100% by weight), the proportion of the 2-nucleus compound in the total content of 2 to 4-nucleus compounds is from 40% to less than 70% by weight, and Tg is lower than 10° C., and especially cresol novolac resins of the following structural formula (4) satisfying these conditions.

(4)



Herein R¹ is hydrogen or methyl, R² is hydrogen or bromine, n is 0 or a natural number, preferably an integer of 0 to 5, more preferably 0, 1 or 2. Since the phenolic resin used herein has one phenolic hydroxyl group in each nucleus, an n-nucleus compound has n phenolic hydroxyl groups in one molecule. If the proportion of the 2-nucleus compound in the total content of 2 to 4-nucleus compounds is more than 70% by weight, the cured composition would have a lower Tg and poor heat resistance. If the proportion of the 2-nucleus

compound in the total content of 2 to 4-nucleus compounds is less than 40% by weight or the total content of 2 to 4-nucleus compounds is less than 80% by weight, indicating a greater proportion of 3- or poly-nucleus compounds, the uncured composition has a higher Tg which deprives the film of its flexibility at room temperature, with a possibility of failure of the film.

In combination with the above-described phenolic resins, any conventional well-known phenolic resin may be used. Such conventional phenolic resins include bisphenol type phenolic resins such as bisphenol A type resins and bisphenol F type resins, phenol and cresol co-condensed novolac resins, trishydroxyphenylalkane type resins such as trishydroxyphenylmethane type resins and trishydroxyphenylpropane type resins, biphenyl type phenolic resin, naphthalene type phenolic resins, cyclopentadiene type phenolic resins, phenolaralkyl resins, and biphenylaralkyl type phenolic resins. These phenolic resins are blended in such amounts that the Tg of the resulting epoxy resin compositions may not exceed 15° C.

Desirably, the phenolic resin is blended with the epoxy resin in such amounts that the equivalent ratio of the phenolic resin to the epoxy resin (that is, the molar ratio of phenolic hydroxyl groups in the phenol resin to epoxy resins in the epoxy resin) may range from 0.5 to 2.0, more desirably from 0.8 to 1.2. If the phenolic resin is blended with the epoxy resin in such amounts that the equivalent ratio may be less than 0.5 or more than 2.0, then the resin composition would not fully cure and hence, lose heat resistance.

Thermoplastic Resin

According to the invention, a thermoplastic resin is blended in the epoxy resin composition. The thermoplastic resin used herein should preferably have a number average molecular weight of 5,000 to 200,000 and a linear molecular structure. As long as these requirements are met, any desired thermoplastic resin may be used. Of these thermoplastic resins, those having a number average molecular weight (Mn) of 10,000 to 100,000 are more preferred. If a thermoplastic resin with a number average molecular weight of less than 5,000 is used, the composition may have a low melt viscosity upon heat molding, so that when a film having a layer of the composition is attached to a substrate or board under pressure or when the film is cured, there might occur, depending on the shape of a device or package and the moderate pressing and curing conditions of the film, a problem that the film loses its original shape or entrapped voids are formed near irregularities on the device. Inversely, if a thermoplastic resin with a number average molecular weight of more than 200,000 is used, the composition may have a too high melt viscosity upon heat molding, so that the composition might fill short near irregularities on the device. If the molecular structure of the thermoplastic resin is branched rather than straight chain, despite the same molecular weight, this thermoplastic resin gives an epoxy resin composition which may have a low melt viscosity upon heating, probably failing to find a good compromise between the flexibility of a film at room temperature and an appropriate melt viscosity upon heating.

Illustrative examples of the thermoplastic resin used herein include AAS resins, AES resins, AS resins, ABS resins, MBS resins, vinyl chloride resins, vinyl acetate resins, methacrylic resins, acrylic resins, phenoxy resins, butadiene resins, various fluoro-resins, polyacetals, various polyamides, polyamide-imides, polyarylates, polyimides, polyether-imides, polyether ether ketones, polyethylene, polyethylene oxide, polyethylene terephthalate,

polycarbonate, polystyrene, polysulfone, polyether sulfone, polyvinyl alcohol, polyvinyl ether, polyvinyl butyral, polyvinyl formal, polyphenylene ether, polyphenylene sulfide, polybutylene terephthalate, polypropylene, and polymethyl pentene.

The thermoplastic resin is blended in such amounts that the composition in an uncured state may have a Tg of lower than 15° C. For instance, a phenoxy resin as used in Example is desirably blended in an amount of 0.1 to 20 parts, more desirably 1 to 10 parts by weight per 100 parts by weight of the resin components (epoxy resin plus phenolic resin) combined, and a polyether sulfone as used in Example is desirably blended in an amount of 0.1 to 10 parts, more desirably 1 to 5 parts by weight per 100 parts by weight of the resin components combined.

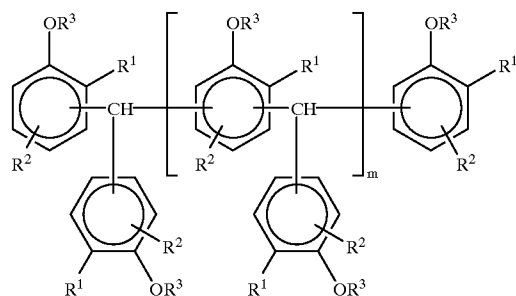
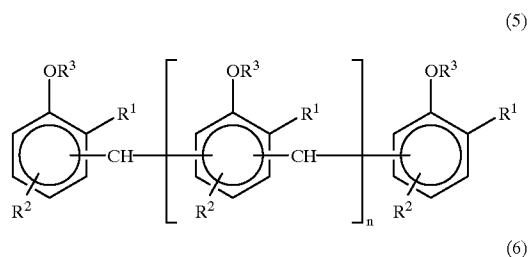
Various additives such as pigments (e.g., carbon black), dyes, flame retardants, and coupling agents may be blended in the epoxy resin composition depending on its particular application.

The epoxy resin composition in an uncured state is soft and rubbery at room temperature (about 25° C.) and has a glass transition temperature (Tg) of lower than 15° C., preferably lower than 10° C. If the Tg of the uncured composition is 15° C. or higher, there is the risk that the film thereof is deprived of its flexibility at room temperature and thus fails.

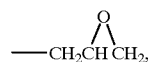
Copolymer

In one preferred embodiment, a copolymer obtained by reacting an aromatic polymer with a specific organopolysiloxane is blended in the epoxy resin composition in order to improve the low stress property thereof.

The aromatic polymers used herein include a variety of compounds, for example, epoxy resins and phenolic resins of the following structural formulae (5) and (6).



Herein, R¹ is hydrogen or methyl, R² is hydrogen or bromine, R³ is hydrogen or glycidyl:

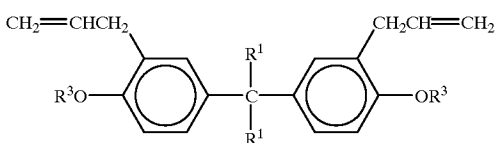
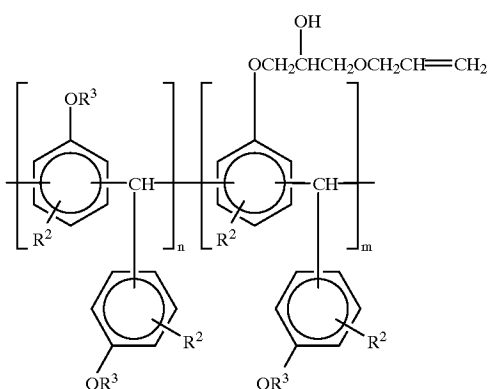
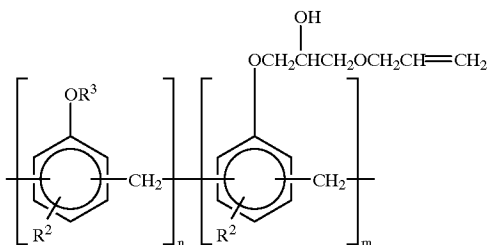


n is 0 or a natural number, preferably an integer of 0 to 50, more preferably an integer of 1 to 20, and m is 0 or a

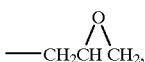
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natural number, preferably an integer of 0 to 5, more preferably 0 or 1.

Other useful aromatic polymers are alkenyl group-bearing compounds (epoxy resins or phenolic resins) having the following structural formulae (7) to (9).



Herein, R¹ is hydrogen or methyl, R² is hydrogen or bromine, R³ is hydrogen or glycidyl:



n and m are natural numbers, preferably the sum of n+m is from 2 to 50, more preferably from 2 to 20.

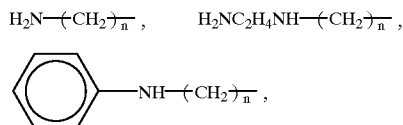
The organopolysiloxane is of the following compositional formula (1).



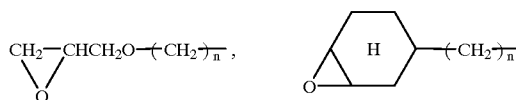
Herein R represents hydrogen, an amino, epoxy, hydroxyl or carboxyl-bearing monovalent hydrocarbon group or an alkoxy group. R' represents a substituted or unsubstituted monovalent hydrocarbon group. The letters a and b are positive numbers satisfying $0.001 \leq a \leq 1$, $1 \leq b \leq 2$, and $1 \leq a+b \leq 3$. The number of silicon atoms in one molecule is from 2 to 1,000, and the number of functional groups R directly attached to silicon atoms in one molecule is at least 1. Differently stated, R is a functional group capable of reacting with epoxy, phenolic hydroxyl or alkenyl groups in the aromatic polymer to form a copolymer.

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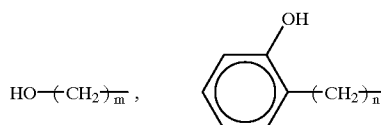
Of the groups represented by R, the amino-bearing monovalent hydrocarbon groups are exemplified by



wherein n is an integer of 1 to 3; the epoxy-bearing monovalent hydrocarbon groups are exemplified by



wherein n is an integer of 1 to 3; the hydroxy-bearing monovalent hydrocarbon groups are exemplified by

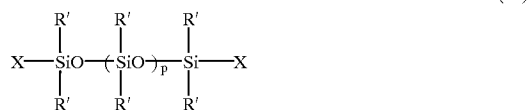
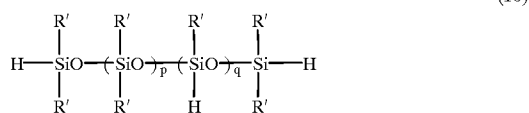


wherein m is an integer of 0 to 3 and n is an integer of 1 to 3; the carboxyl-bearing monovalent hydrocarbon groups are exemplified by $-C_xH_{2x}COOH$ wherein x is an integer of 0 to 10; and the alkoxy groups are exemplified by those of 1 to 4 carbon atoms such as methoxy, ethoxy, and n-propoxy.

The substituted or unsubstituted monovalent hydrocarbon groups represented by R' are preferably those of 1 to 10 carbon atoms, for example, alkyl groups such as methyl, ethyl, n-propyl, isopropyl, n-butyl, isobutyl, tert-butyl, pentyl, neopentyl, hexyl, cyclohexyl, octyl and decyl; alkenyl groups such as vinyl, allyl, propenyl and butenyl; aryl groups such as phenyl and tolyl; aralkyl groups such as benzyl and phenylethyl; and halo-substituted monovalent hydrocarbon groups obtained by substituting halogen atoms for some or all of the hydrogen atoms on the foregoing hydrocarbon groups.

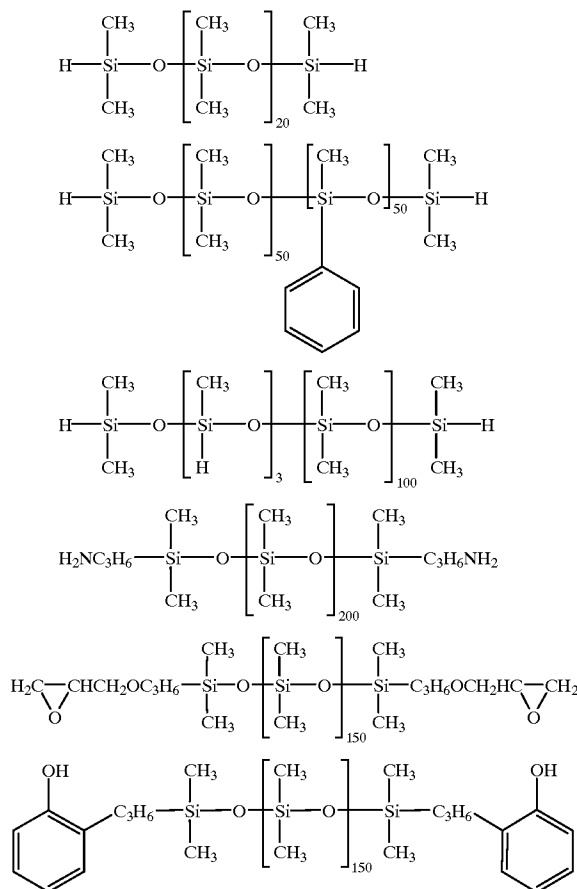
Preferably, letters a and b satisfy $0.01 \leq a \leq 0.1$, $1.8 \leq b \leq 2$, and $1.85 \leq a+b \leq 2.1$, and the number of silicon atoms is from 10 to 400, more preferably from 20 to 210.

Illustrative examples of the organopolysiloxane are compounds of the following structures.



In formulae (10) and (11), R' represents a substituted or unsubstituted monovalent hydrocarbon group as in formula (1), preferably methyl or phenyl; X represents an amino, epoxy, hydroxyl or carboxyl-bearing monovalent hydrocarbon group; p is an integer of 0 to 1,000, preferably 8 to 400; and q is an integer of 0 to 20, preferably 0 to 5.

Specific examples are diorganopolysiloxane as given below.



Desirably the organopolysiloxane has a molecular weight of 100 to 70,000 though not critical. When a copolymer obtained from an organopolysiloxane having a molecular weight of 100 to 70,000 is blended in an epoxy resin composition, the copolymer is not compatible with the matrix and rather forms a fine island-in-sea structure. If the molecular weight is less than 100, the resulting copolymer would become compatible with the matrix so that the island-in-sea structure disappears. If the molecular weight is greater than 70,000, an enlarged island-in-sea structure would form. In either case, the cured composition would lose the desired low stress property.

Any well-known method may be used in reacting the aromatic polymer with the organopolysiloxane to form a copolymer.

An appropriate amount of the copolymer blended is 0 to about 100 parts, more preferably about 1 to 50 parts by weight per 100 parts by weight of the epoxy resin (or the epoxy resin plus the phenolic resin, if the phenolic resin is blended). Especially for the phenolic curing type epoxy resin compositions, the ratio of the total content of phenolic hydroxyl groups to the total content of epoxy groups in the entirety of the epoxy resin, phenolic resin and copolymer is desirably from 0.5 to 2.0, more desirably from 0.8 to 1.2. If the total phenolic hydroxyl group content relative to the total epoxy group content is outside this range, the resin composition would not fully cure and hence, lose heat resistance.

The epoxy resin composition can be obtained by uniformly agitating and mixing the predetermined amounts of

the above-described components, working the mixture in a roll mill, kneader or continuous kneader preheated at 70 to 90° C., cooling the mixture below its Tg, and grinding the mixture. The order of blending the components is not critical although it is desirable to premix the thermoplastic resin with the epoxy resin or phenolic resin. That is, the thermoplastic resin and the epoxy resin or phenolic resin are mixed along with a solvent in which both the resins are soluble, until uniform, whereupon the solvent is removed from the premix. Alternatively, predetermined amounts of the thermoplastic resin and the epoxy resin or phenolic resin are mixed in a kneader which is preheated above the Tg of the thermoplastic resin, until a uniform premix is obtained. Thereafter, the premix is mixed with the remaining components in a roll mill, kneader or continuous kneader which is preheated at 70 to 90° C., whereupon the mixture is cooled below its Tg and ground.

The epoxy resin composition is advantageously used in film form. As to the conditions under which the composition is heat molded into a film, the pressure applied to the composition is very low as compared with the transfer molding of conventional solid resins, and the composition has a more chance to be abruptly exposed to high temperatures as compared with the potting and under-filling of liquid materials. Therefore, volatile components in the uncured composition tend to be left as voids at the end of curing. It is thus desired to minimize the volatile content. Preferably, the volatile content is 0.1% by weight or lower, and more preferably 0.01% by weight or lower.

The epoxy resin composition of the invention is effectively used in semiconductor packaging, preferably after the composition is formed into a film. More preferably, a laminate film comprising at least two layers is contemplated wherein the epoxy resin composition is used as at least one layer thereof. The film or layer made of the epoxy resin composition preferably has a thickness of 20 to 150 μm. The material and thickness of the remaining layers are selected in accordance with the particular application of the laminate film.

One specific example is a laminate film consisting of a layer of the epoxy resin composition and a protective sheet which is bonded to one surface or each surface of the layer for the purpose of protecting the layer, examples of the protective sheet being a silicone sheet, Teflon® sheet, or polyethylene terephthalate (PET) sheet having parting silicone or Teflon® coated on its surface. Another exemplary laminate film has a layer of adhesive between the layer of the epoxy resin composition and the protective sheet or sheets, the adhesive layer serving to providing a quick bond to a substrate or semiconductor chip at room temperature.

The laminate film is manufactured by means of a coater/laminator as used in the manufacture of conventional rubber sheets. More specifically, the epoxy resin composition is stretched under heat and pressure, cut into strips or sliced into tapes (which are wound) depending on the particular application of the laminate film. Depending on the application, the strip or tape is further cut to the desired shape, which is used after the protective sheet is removed.

The laminate film is applicable to any semiconductor device although it is advantageously applied to small, thin semiconductor devices such as CSP. The laminate film is effective in establishing a bond in the narrow gap between a chip and a substrate. As compared with conventional acid anhydride curing type or amine curing type compositions, the inventive composition is effective in forming a reliable bond. The manner of using the laminate film is not critical. One typical procedure involves cutting the laminate film to

TABLE 1

Dispersity, epoxy equivalent, Tg of epoxy resin								
	2-nucleus	3-nucleus	4-nucleus	5-nucleus	6 and poly-nucleus	Mw/Mn	Epoxy equivalent	Tg (° C.)
A	9	40	13	9	20	1.5	187	9
B	10	32	13	10	35	1.7	190	11
C	13	13	12	10	52	2.1	199	13
D	4	7	29	12	48	1.7	191	25
E	9	38	12	9	32	1.6	180	8
F	—	52	—	19	29	1.7	164	11

A to D: cresol novolac type epoxy resins
 E: phenol novolac type epoxy resin
 F: trishydroxyphenylmethane type epoxy resin
 Unit: % by weight for 2 to 5-nucleus compounds and 6 and poly-nucleus compounds

TABLE 2

Dispersity, phenol equivalent, Tg of phenolic resin							
	2-nucleus	3-nucleus	4-nucleus	5-nucleus	Mw/Mn	Epoxy equivalent	Tg (° C.)
A	60	28	9	3	1.2	110	9
B	31	29	17	19	1.4	112	14
C	6	25	25	44	1.2	113	22
D	37	27	16	20	1.3	110	8

A to C: cresol novolac resins
 D: phenol novolac resin
 Unit: % by weight for 2 to 4-nucleus compounds and 5 and poly-nucleus compounds

These epoxy resin compositions were examined by the following tests (a) to (h). The results are shown in Tables 3 to 7.

(a) Tg of Uncured Composition

By differential scanning calorimetry (DSC), 10 mg of an uncured composition was heated at a rate of 5° C./min and the maximum of specific heat was measured.

(b) Film Handling

An uncured composition was formed into film strips of 10 mm×50 mm×0.1 mm. Each strip was folded at 25° C. such that the short sides (10 mm) coincided with each other. The number of broken strips was reported per the total number of tested strips.

(c) Tg of Cured Composition

A composition was molded at 150° C. and 50 kgf/cm² for 3 minutes into a specimen of 5 mm×5 mm×15 mm, which was postcured at 150° C. for 4 hours. Tg was measured by means of TMA by heating the specimen at a rate of 5° C./min.

(d) Moisture Resistance

A semiconductor package by fabrication procedure A or C was allowed to stand for 24 and 48 hours in an atmosphere of 121° C., RH 100% and 2 atm. Some package samples showed abnormal values because of line disconnection. The number of failed samples per the total number of tested samples is reported.

(e) Water Absorption

A composition was molded at 150° C. and 50 kgf/cm² for 3 minutes into a disk having a diameter of 50 mm and a thickness of 3 mm, which was postcured at 150° C. for 4 hours. The disk was allowed to stand for 24 hours in an atmosphere of 121° C., RH 100% and 2 atm. A weight change was determined.

(f) Solder Cracking Resistance After Moisture Absorption

A semiconductor package by fabrication procedure A or C was allowed to stand for 24 hours in an atmosphere of 121°

C., RH 100% and 2 atm. It was immersed for 10 seconds in a solder bath at 240° C. The number of cracked samples per the total number of tested samples is reported.

(g) Volatile Content of Uncured Composition

After 5 g of an uncured composition was heated at 180° C. for one hour, a weight change was determined.

(h) Voids of Cured Composition

Using an ultrasonic flaw detector, a semiconductor package by fabrication procedure A, B, C or D was inspected to determine the void area per the total area of the package. The sample in which the film lost its original shape due to resin flow is labeled "Flow."

Referring to FIG. 1, there is illustrated a semiconductor device package comprising a BT substrate 1, an epoxy resin composition film 2, solder bumps 3, a silicon chip 4, gold terminals 5, and copper leads 6.

Fabrication Procedure A

As shown in FIG. 2, the epoxy resin composition film 2 of 10 mm×10 mm×0.1 mm was placed on the BT substrate 1, moderately pressed thereto at 80° C. and 0.1 kgf/cm² for 5 seconds, and preheated at 120° C. for 10 seconds. The silicon chip 4 of 10 mm×10 mm×0.3 mm having aluminum wiring and solder bumps 3 formed thereon was positioned on the film. The film was heat molded at 180° C. and 10 kgf/cm² for 10 seconds and postcured at 150° C. for one hour, completing the semiconductor package shown in FIG. 1.

Fabrication Procedure B

As shown in FIG. 2, the epoxy resin composition film 2 of 10 mm×10 mm×0.1 mm was placed on the BT substrate 1, moderately pressed thereto at 80° C. and 0.1 kgf/cm² for 5 seconds, and preheated at 120° C. for 10 seconds. The silicon chip 4 of 10 mm×10 mm×0.3 mm having aluminum wiring and solder bumps 3 formed thereon was positioned on the film. The film was heat molded at 180° C. and 30 kgf/cm² for 10 seconds and postcured at 150° C. for one hour, completing the semiconductor package shown in FIG. 1.

Fabrication Procedure C

As shown in FIG. 3, the epoxy resin composition film 2 of 10 mm×10 mm×0.1 mm was placed on the BT substrate 1 having solder bumps 3 formed thereon, moderately pressed thereto at 80° C. and 1 kgf/cm² for 5 seconds, and preheated at 120° C. for 10 seconds. The silicon chip 4 of 10 mm×10 mm×0.3 mm having aluminum wiring formed thereon was positioned on the film. The film was heat molded at 180° C. and 10 kgf/cm² for 10 seconds and postcured at 150° C. for one hour, completing the semiconductor package shown in FIG. 1.

Fabrication Procedure D

As shown in FIG. 3, the epoxy resin composition film 2 of 10 mm×10 mm×0.1 mm was placed on the BT substrate 1 having solder bumps 3 formed thereon, moderately pressed thereto at 80° C. and 1 kgf/cm² for 5 seconds, and preheated at 120° C. for 10 seconds. The silicon chip 4 of 10 mm×10 mm×0.3 mm having aluminum wiring formed thereon was positioned on the film. The film was heat molded at 180° C. and 30 kgf/cm² for 10 seconds and postcured at 150° C. for one hour, completing the semiconductor package shown in FIG. 1.

TABLE 3

	E1	E2	E3	E4	E5	E6
Epoxy resin A	69.4	64.4	59.4	54.4	69.4	64.4
Epoxy resin B	0	0	0	0	0	0
Epoxy resin C	0	0	0	0	0	0
Epoxy resin D	0	0	0	0	0	0
Epoxy resin E	0	0	0	0	0	0
Epoxy resin F	0	0	0	0	0	0
Phenolic resin A	0	0	0	0	0	0
Phenolic resin B	0	0	0	0	0	0
Phenolic resin C	0	0	0	0	0	0
Phenolic resin D	0	0	0	0	0	0
Phenoxy resin	5.0	10.0	15.0	20.0	0	0
PES	0	0	0	0	5.0	10.0
Copolymer	25.6	25.6	25.6	25.6	25.6	25.6
Spherical silica	300	300	300	300	300	300
2PZ	2.0	2.0	2.0	2.0	2.0	2.0
TPP	0	0	0	0	0	0
KBM403	1.0	1.0	1.0	1.0	1.0	1.0
(a) Tg of uncured composition, ° C.	10	11	12	14	12	14
(b) Film handling	0/5	0/5	0/5	0/5	0/5	0/5
(c) Tg of cured composition, ° C.	146	145	144	142	147	149
(d) Moisture resistance A @ 48 hr.	0/20	0/20	0/20	0/20	0/20	0/20
(d) Moisture resistance C @ 48 hr.	0/20	0/20	0/20	0/20	0/20	0/20
(e) Water absorption, wt %	0.66	0.66	0.65	0.64	0.66	0.65
(f) Solder cracking resistance after moisture absorption A	0/20	0/20	0/20	0/20	0/20	0/20
(f) Solder cracking resistance after moisture absorption C	0/20	0/20	0/20	0/20	0/20	0/20
(g) Volatile content of uncured composition, wt %	0.01	0.01	0.01	0.01	0.01	0.01
(h) Voids in semiconductor package A, area %	0.05	0.04	0.04	0.03	0.04	0.03
(h) Voids in semiconductor package B, area %	0.03	0.03	0.02	0.02	0.03	0.02
(h) Voids in semiconductor package C, area %	0.10	0.09	0.08	0.08	0.09	0.09
(h) Voids in semiconductor package D, area %	0.06	0.06	0.95	0.05	0.06	0.06

TABLE 4

	E7	E8	E9	E10	E11	E12
Epoxy resin A	37.6	34.5	31.3	28.2	37.6	34.5
Epoxy resin B	0	0	0	0	0	0
Epoxy resin C	0	0	0	0	0	0
Epoxy resin D	0	0	0	0	0	0
Epoxy resin E	0	0	0	0	0	0
Epoxy resin F	0	0	0	0	0	0
Phenolic resin A	31.8	29.9	28.1	26.2	31.8	29.9
Phenolic resin B	0	0	0	0	0	0
Phenolic resin C	0	0	0	0	0	0
Phenolic resin D	0	0	0	0	0	0
Phenoxy resin	5.0	10.0	15.0	20.0	0	0
PES	0	0	0	0	5.0	10.0
Copolymer	25.6	25.6	25.6	25.6	25.6	25.6

TABLE 4-continued

	E7	E8	E9	E10	E11	E12
5 Spherical silica	300	300	300	300	300	300
2PZ	0	0	0	0	0	0
TPP	1.0	1.0	1.0	1.0	1.0	1.0
KBM403	1.0	1.0	1.0	1.0	1.0	1.0
(a) Tg of uncured composition, ° C.	10	11	12	13	11	14
10 (b) Film handling	0/5	0/5	0/5	0/5	0/5	0/5
(c) Tg of cured composition, ° C.	132	131	131	136	134	136
(d) Moisture resistance A @ 48 hr.	0/20	0/20	0/20	0/20	0/20	0/20
(d) Moisture resistance C @ 48 hr.	0/20	0/20	0/20	0/20	0/20	0/20
15 (e) Water absorption, wt %	0.61	0.61	0.60	0.60	0.61	0.61
(f) Solder cracking resistance after moisture absorption A	0/20	0/20	0/20	0/20	0/20	0/20
(f) Solder cracking resistance after moisture absorption C	0/20	0/20	0/20	0/20	0/20	0/20
20 (g) Volatile content of uncured composition, wt %	0.01	0.01	0.01	0.01	0.01	0.01
(h) Voids in semiconductor package A, area %	0.05	0.05	0.04	0.04	0.04	0.04
(h) Voids in semiconductor package B, area %	0.03	0.03	0.03	0.02	0.03	0.02
(h) Voids in semiconductor package C, area %	0.11	0.11	0.10	0.09	0.11	0.10
(h) Voids in semiconductor package D, area %	0.07	0.06	0.06	0.05	0.07	0.06

TABLE 5

	E13	E14	E15	E16	E17	E18
35 Epoxy resin A	0	0	0	37.2	0	0
Epoxy resin B	69.4	0	0	0	37.8	37.5
Epoxy resin C	0	0	0	0	0	0
Epoxy resin D	0	0	0	0	0	0
Epoxy resin E	0	69.4	0	0	0	0
Epoxy resin F	0	0	69.4	0	0	0
40 Phenolic resin A	0	0	0	0	31.6	0
Phenolic resin B	0	0	0	32.2	0	31.9
Phenolic resin C	0	0	0	0	0	0
Phenolic resin D	0	0	0	0	0	0
Phenoxy resin	5.0	5.0	5.0	5.0	5.0	5.0
PES	0	0	0	0	0	0
45 Copolymer	25.6	25.6	25.6	25.6	25.6	25.6
Spherical silica	300	300	300	300	300	300
2PZ	2.0	2.0	2.0	0	0	0
TPP	0	0	0	1.0	1.0	1.0
KBM403	1.0	1.0	1.0	1.0	1.0	1.0
(a) Tg of uncured composition, ° C.	11	8	13	12	11	13
50 (b) Film handling	0/5	0/5	0/5	0/5	0/5	0/5
(c) Tg of cured composition, ° C.	145	142	144	131	130	130
(d) Moisture resistance A @ 48 hr.	0/20	0/20	0/20	0/20	0/20	0/20
(d) Moisture resistance C @ 48 hr.	0/20	0/20	0/20	0/20	0/20	0/20
(e) Water absorption, wt %	0.66	0.68	0.69	0.60	0.60	0.61
(f) Solder cracking resistance after moisture absorption A	0/20	0/20	0/20	0/20	0/20	0/20
(f) Solder cracking resistance after moisture absorption C	0/20	0/20	0/20	0/20	0/20	0/20
60 (g) Volatile content of uncured composition, wt %	0.02	0.02	0.03	0.03	0.02	0.03
(h) Voids in semiconductor package A, area %	0.07	0.08	0.11	0.12	0.07	0.10
(h) Voids in semiconductor package B, area %	0.04	0.04	0.05	0.06	0.03	0.04

TABLE 5-continued

	E13	E14	E15	E16	E17	E18
(h) Voids in semiconductor package C, area %	0.15	0.16	0.20	0.20	0.16	0.18
(h) Voids in semiconductor package D, area %	0.11	0.11	0.12	0.13	0.11	0.12

TABLE 6

	E19	E20	CE1	CE2	CE3	CE4
Epoxy resin A	0	0	74.4	49.4	59.4	40.5
Epoxy resin B	0	0	0	0	0	0
Epoxy resin C	0	0	0	0	0	0
Epoxy resin D	0	0	0	0	0	0
Epoxy resin E	37.1	0	0	0	0	0
Epoxy resin F	0	35.7	0	0	0	0
Phenolic resin A	0	33.7	0	0	0	33.6
Phenolic resin B	0	0	0	0	0	0
Phenolic resin C	0	0	0	0	0	0
Phenolic resin D	32.3	0	0	0	0	0
Phenoxy resin	5.0	5.0	0	25.0	0	0
PES	0	0	0	0	15.0	0
Copolymer	25.6	25.6	25.6	25.6	25.6	25.6
Spherical silica	300	300	300	300	300	300
2PZ	0	0	2.0	2.0	2.0	0
TPP	1.0	1.0	0	0	0	1.0
KBM403	1.0	1.0	1.0	1.0	1.0	1.0
(a) Tg of uncured composition, ° C.	id	12	9	16	17	9
(b) Film handling	0/5	0/5	0/5	5/5	5/5	0/5
(c) Tg of cured composition, ° C.	131	140	146	—	—	132
(d) Moisture resistance A @ 48 hr	0/20	0/20	0/20	—	—	0/20
(d) Moisture resistance C @ 48 hr	0/20	0/20	9/20	—	—	7/20
(e) Water absorption, wt %	0.66	0.68	0.66	—	—	0.61
(f) Solder cracking resistance after moisture absorption A	0/20	0/20	0/20	—	—	0/20
(f) Solder cracking resistance after moisture absorption C	0/20	0/20	11/20	—	—	10/20
(g) Volatile content of uncured composition, wt %	0.07	0.05	0.01	—	—	0.01
(h) Voids in semiconductor package A, area %	0.20	0.15	0.05	—	—	0.05
(h) Voids in semiconductor package B, area %	0.12	0.09	Flow	—	—	Flow
(h) Voids in semiconductor package C, area %	0.30	0.24	0.52	—	—	0.48
(h) Voids in semiconductor package D, area %	0.18	0.16	Flow	—	—	Flow

TABLE 7

	CE5	CE6	CE7	CE8	CE9
Epoxy resin A	0	0	37.1	0	0
Epoxy resin B	0	0	0	0	0
Epoxy resin C	69.4	0	0	38.5	0
Epoxy resin D	0	69.4	0	0	37.9
Epoxy resin E	0	0	0	0	0
Epoxy resin F	0	0	0	0	0
Phenolic resin A	0	0	0	30.9	31.5
Phenolic resin B	0	0	0	0	0
Phenolic resin C	0	0	32.3	0	0
Phenolic resin D	0	0	0	0	0
Phenoxy resin	5.0	5.0	5.0	5.0	5.0
PES	0	0	0	0	0
Copolymer	25.6	25.6	25.6	25.6	25.6
Spherical silica	300	300	300	300	300
2PZ	2.0	2.0	0	0	0

TABLE 7-continued

	CE5	CE6	CE7	CE8	CE9
TPP	0	0	1.0	0	0
KBM403	1.0	1.0	1.0	1.0	1.0
(a) Tg of uncured composition, ° C.	13	21	16	12	18
(b) Film handling	0/5	5/5	5/5	0/5	5/5
(c) Tg of cured composition, ° C.	134	—	—	114	—
(d) Moisture resistance A @ 48 hr	0/20	—	—	0/20	—
(d) Moisture resistance C @ 48 hr	15/20	—	—	17/20	—
(e) Water absorption, wt %	0.72	—	—	0.61	—
(f) Solder cracking resistance after moisture absorption A	2/20	—	—	2/20	—
(f) Solder cracking resistance after moisture absorption C	20/20	—	—	20/20	—
(g) Volatile content of uncured composition, wt %	0.11	—	—	0.12	—
(h) Voids in semiconductor package A, area %	0.50	—	—	0.50	—
(h) Voids in semiconductor package B, area %	0.32	—	—	0.28	—
(h) Voids in semiconductor package C, area %	0.98	—	—	1.01	—
(h) Voids in semiconductor package D, area %	0.62	—	—	0.68	—

Japanese Patent Application No. 11-106571 is incorporated herein by reference.

Although some preferred embodiments have been described, many modifications and variations may be made thereto in light of the above teachings. It is therefore to be understood that the invention may be practiced otherwise than as specifically described without departing from the scope of the appended claims.

What is claimed is:

1. An epoxy resin composition comprising

(A) an epoxy resin containing up to 10% by weight of a 2-nucleus compound and at least 50% by weight of 3 to 5-nucleus compounds combined and having a dispersity of up to 1.7,

(B) an inorganic filler,

(C) a curing catalyst, and

(D) a thermoplastic resin, said composition in an uncured state having a glass transition temperature of lower than 15° C.

2. The epoxy resin composition of claim 1 wherein the thermoplastic resin (D) has a number average molecular weight of 5,000 to 200,000 and a linear molecular structure.

3. The epoxy resin composition of claim 1 wherein the curing catalyst (C) is an imidazole.

4. The epoxy resin composition of claim 1 further comprising (E) a phenolic resin.

5. The epoxy resin composition of claim 4 wherein the phenolic resin (E) has a glass transition temperature of lower than 15° C. and is free of a monomer.

6. The epoxy resin composition of claim 1 further comprising a copolymer obtained by reacting an aromatic polymer with an organopolysiloxane of the following compositional formula (1):



wherein R represents hydrogen, an amino, epoxy, hydroxyl or carboxyl group-bearing monovalent hydrocarbon group, or an alkoxy group, R' represents a substituted or unsubsti-

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tuted monovalent hydrocarbon group, "a" is a positive number of 0.001 to 1, "b" is a positive number of 1 to 2, and the sum of "a" and "b" is from 1 to 3, the number of silicon atoms in one molecule is 2 to 1,000, and the number of functional groups R directly attached to silicon atoms in one molecule is at least 1.

7. The epoxy resin composition of claim 1 which in an uncured state has a volatile content of up to 0.1% by weight.

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8. A laminate film comprising at least two layers, at least one of which is formed of the epoxy resin composition of any one of claims 1 to 7 to a thickness of 20 to 150 μm .

9. A semiconductor device comprising a semiconductor chip having a surface sealed with the laminate film of claim 8 in a cured state.

* * * * *